

[Abstract]

According to one embodiment, the semiconductor device includes a stacked body and a column-shaped portion. The stacked body includes a first stacked portion including a plurality of electrode layers stacked in a first direction via an insulator, a second stacked portion including a plurality of electrode layers stacked in the first direction via an insulator and being disposed separately from the first stacked portion in the first direction, and a connection portion including a high dielectric layer provided between the first stacked portion and the second stacked portion and having a dielectric constant higher than a dielectric constant of the insulator. The column-shaped portion includes a first portion provided in the first stacked portion and extending in the first direction of the stacked body, a second portion provided in the second stacked portion and extending in the first direction, and an intermediate portion provided in the connection portion and connected the first portion to the second portion.